

# FDS2170N3

## 200V N-Channel PowerTrench® MOSFET

### General Description

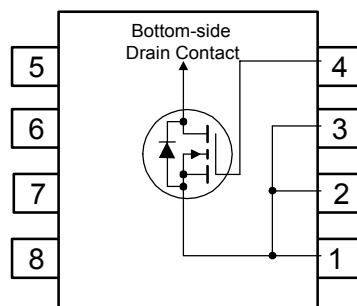
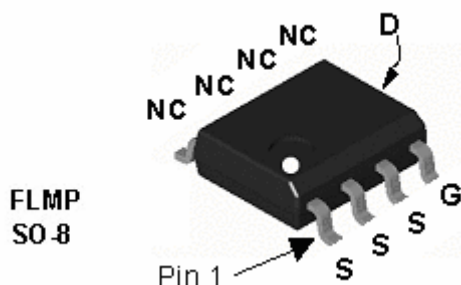
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for "low side" synchronous rectifier operation, providing an extremely low  $R_{DS(ON)}$  in a small package.

### Applications

- Synchronous rectifier
- DC/DC converter

### Features

- 3.0 A, 200 V.  $R_{DS(ON)} = 128 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$
- High performance trench technology for extremely low  $R_{DS(ON)}$
- High power and current handling capability
- Fast switching, low gate charge (26nC typical)
- FLMP SO-8 package: Enhanced thermal performance in industry-standard package size



### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	200	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous (Note 1a)	3.0	A
	– Pulsed	20	
$P_D$	Power Dissipation for Single Operation (Note 1a) (Note 1b)	3.0	W
		1.8	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	40	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	0.5	

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS2170N3	FDS2170N3	13"	12mm	2500 units

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Drain-Source Avalanche Ratings (Note 2)

$W_{DSS}$	Drain-Source Avalanche Energy	Single Pulse, $V_{DD} = 100\text{ V}$ , $I_D = 3.0\text{ A}$			370	mJ
$I_{AR}$	Drain-Source Avalanche Current				3	A

### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$ , $I_D = 250\ \mu\text{A}$	200			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		231		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 160\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage, Forward	$V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate-Body Leakage, Reverse	$V_{GS} = -20\text{ V}$ , $V_{DS} = 0\text{ V}$			-100	nA

### On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	2	4	4.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-10		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 3.0\text{ A}$ $V_{GS} = 10\text{ V}$ , $I_D = 3.0\text{ A}$ , $T_J = 125^\circ\text{C}$		108 214	128 268	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}$ , $I_D = 3.0\text{ A}$		15		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 100\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		1292		pF
$C_{oss}$	Output Capacitance			72		pF
$C_{rss}$	Reverse Transfer Capacitance			24		pF
$R_G$	Gate Resistance	$V_{GS} = 15\text{ mV}$ , $f = 1.0\text{ MHz}$		1.5		$\Omega$

### Switching Characteristics (Note 2)

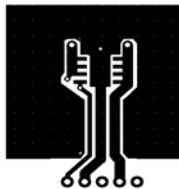
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{ V}$ , $I_D = 1\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\ \Omega$		12	22	ns
$t_r$	Turn-On Rise Time			5	10	ns
$t_{d(off)}$	Turn-Off Delay Time			30	48	ns
$t_f$	Turn-Off Fall Time			23	36	ns
$Q_g$	Total Gate Charge	$V_{DS} = 100\text{ V}$ , $I_D = 3.0\text{ A}$ , $V_{GS} = 10\text{ V}$		26	36	nC
$Q_{gs}$	Gate-Source Charge			7		nC
$Q_{gd}$	Gate-Drain Charge			10		nC

### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current			2.5	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}$ , $I_S = 2.5\text{ A}$ (Note 2)		0.76	1.2	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 3.0\text{ A}$		95		nS
$Q_{rr}$	Diode Reverse Recovery Charge	$dI_F/dt = 100\text{ A}/\mu\text{s}$ (Note 2)		552		nC

#### Notes:

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $40^\circ\text{C/W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper

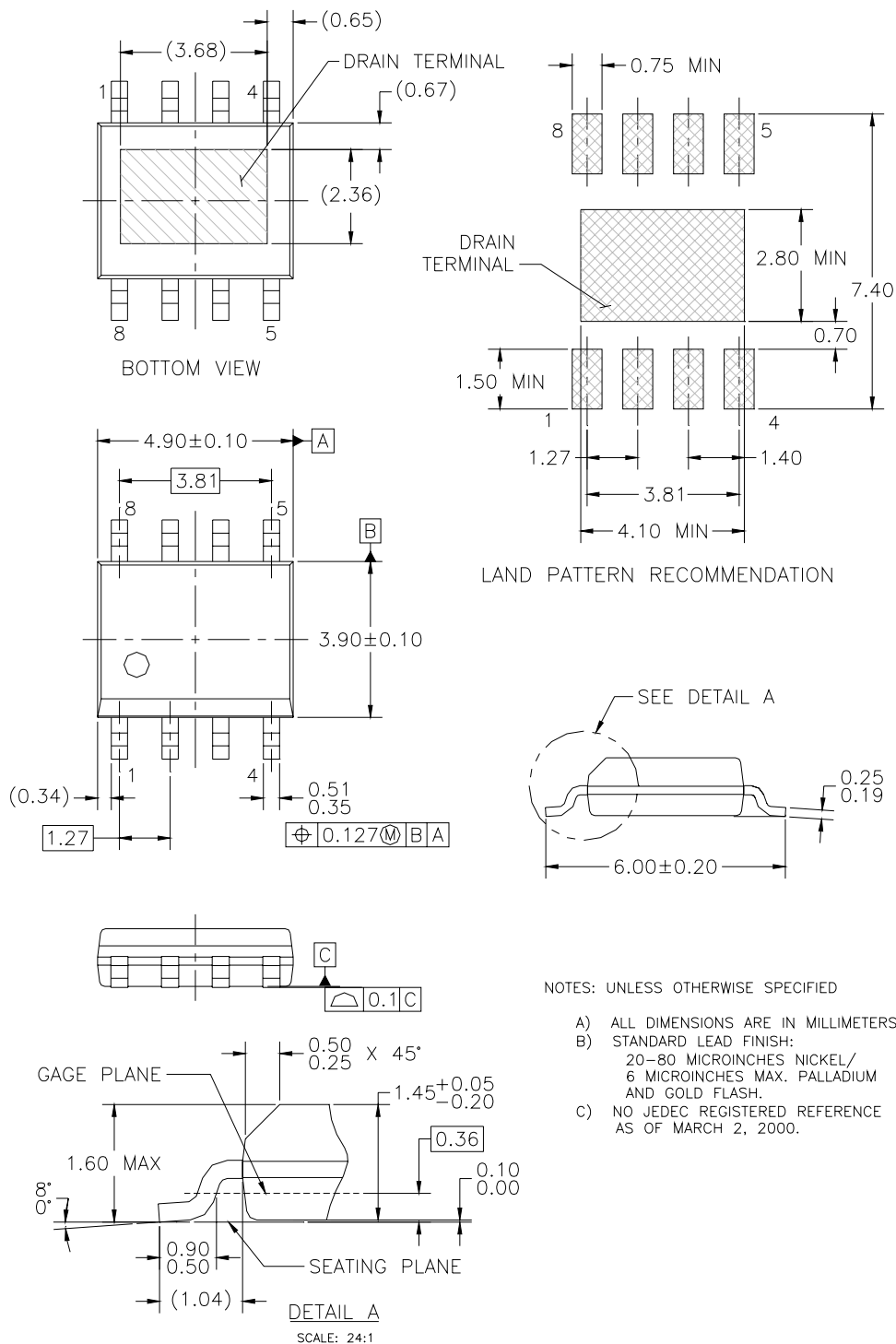


b)  $85^\circ\text{C/W}$  when mounted on a minimum pad of 2 oz copper

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2.0%

### Dimensional Outline and Pad Layout



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) ALL DIMENSIONS ARE IN MILLIMETERS.
  - B) STANDARD LEAD FINISH:  
20-80 MICROINCHES NICKEL/  
6 MICROINCHES MAX. PALLADIUM  
AND GOLD FLASH.
  - C) NO JEDEC REGISTERED REFERENCE  
AS OF MARCH 2, 2000.

## Typical Characteristics

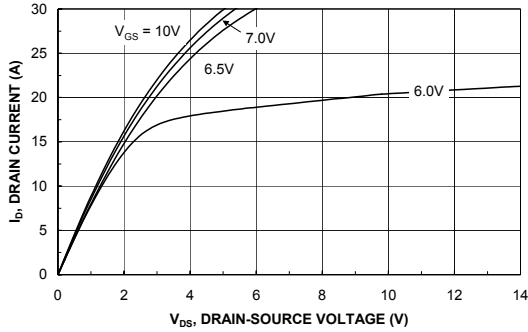


Figure 1. On-Region Characteristics.

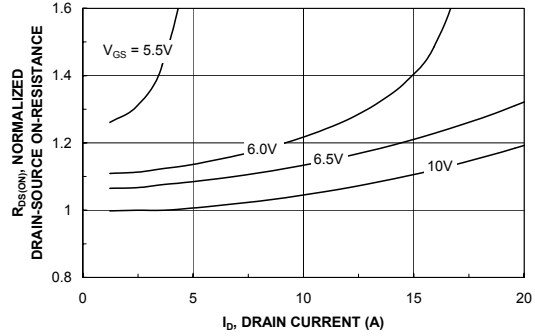


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

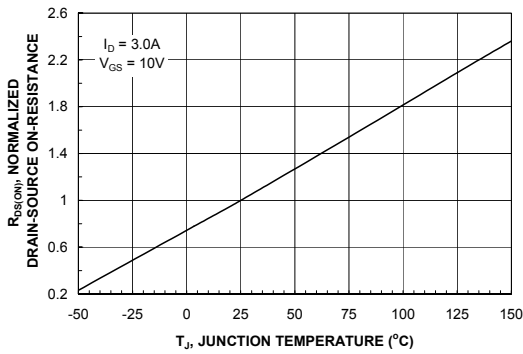


Figure 3. On-Resistance Variation with Temperature.

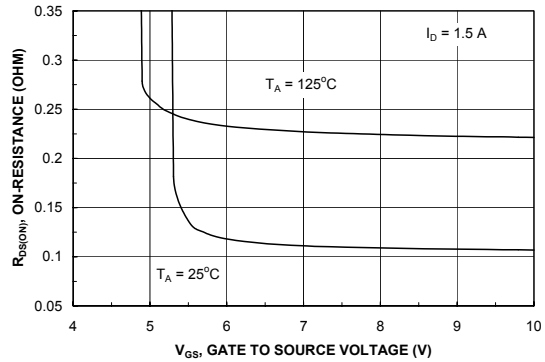


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

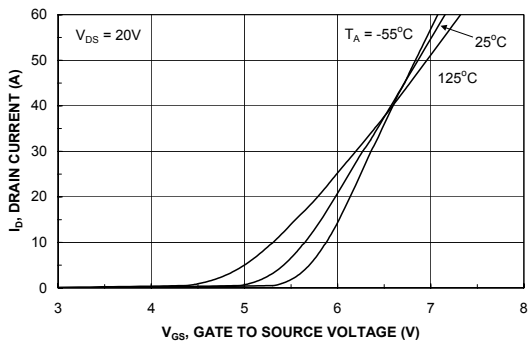


Figure 5. Transfer Characteristics.

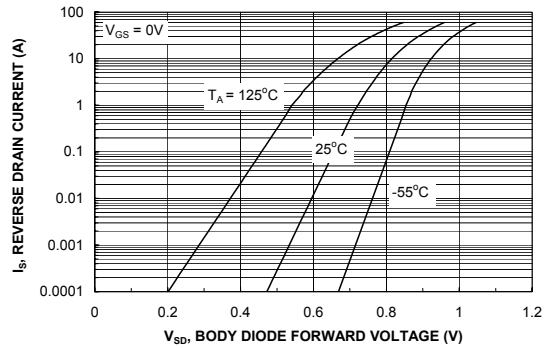


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

### Typical Characteristics

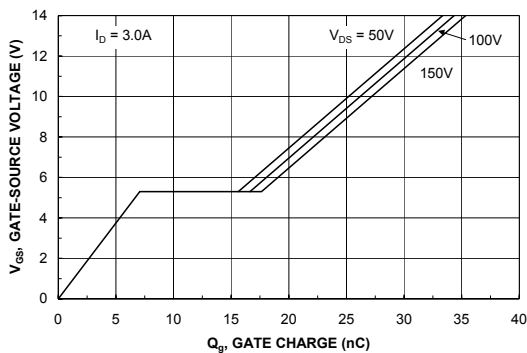


Figure 7. Gate Charge Characteristics.

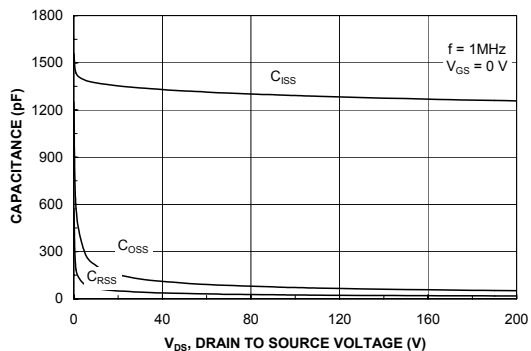


Figure 8. Capacitance Characteristics.

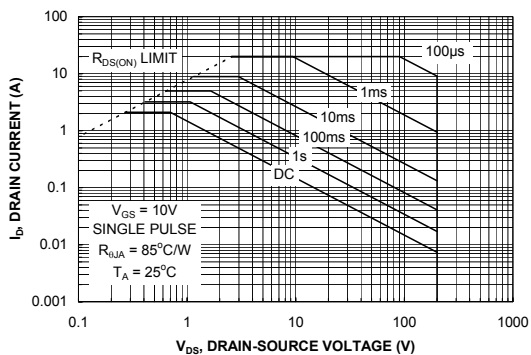


Figure 9. Maximum Safe Operating Area.

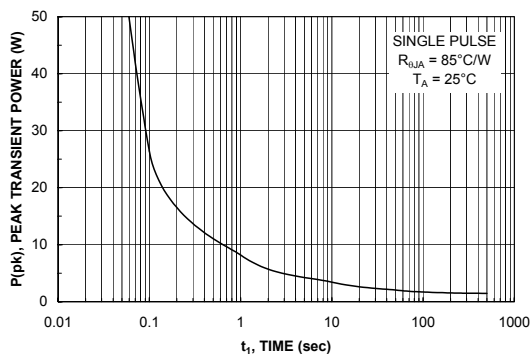


Figure 10. Single Pulse Maximum Power Dissipation.

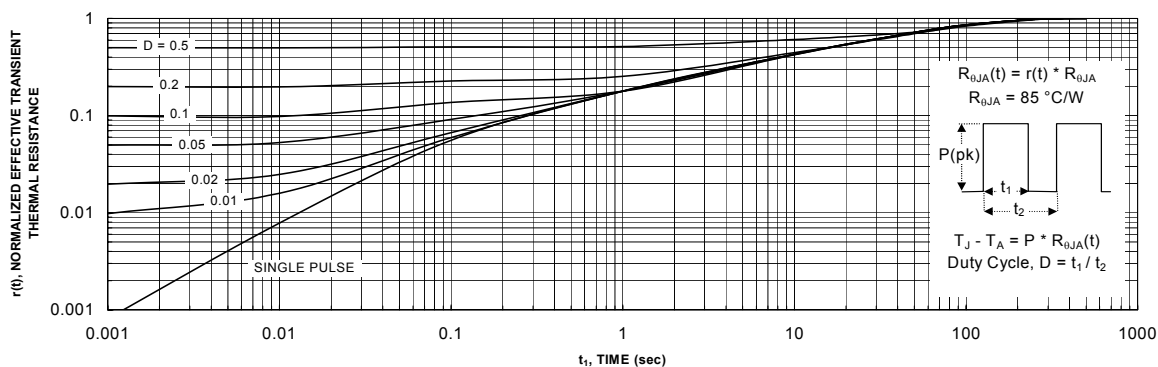


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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